

# Low frequency amplifier

## QST7

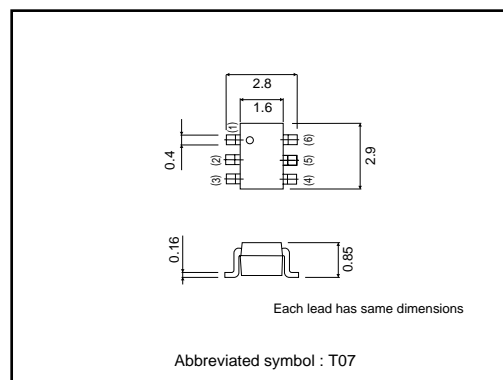
### ●Application

Low frequency amplifier  
Driver

### ●Features

- 1) A collector current is large.
- 2)  $V_{CE(sat)} \leq -370\text{mV}$   
At  $I_C = -1\text{A} / I_B = -50\text{mA}$

### ●External dimensions (Units : mm)



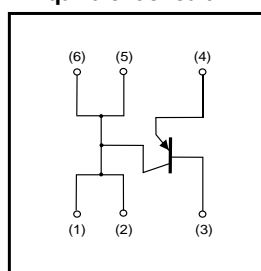
### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CB0}$	-30	V
Collector-emitter voltage	$V_{CEO}$	-30	V
Emitter-base voltage	$V_{EB0}$	-6	V
Collector current	$I_C$	-1.5	A
	$I_{CP}$	-3	A*1
Power dissipation	$P_C$	500	mW*2
Junction temperature	$T_j$	150	°C
Range of storage temperature	$T_{stg}$	-55~+150	°C

\*1 Single pulse,  $P_w=1\text{ms}$

\*2 Each Terminal Mounted on a Recommended

### ●Equivalent circuit



### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CB0}$	-30	-	-	V	$I_C = -10\mu\text{A}$
Collector-emitter breakdown voltage	$BV_{CEO}$	-30	-	-	V	$I_C = -1\text{mA}$
Emitter-base breakdown voltage	$BV_{EB0}$	-6	-	-	V	$I_E = -10\mu\text{A}$
Collector cutoff current	$I_{CBO}$	-	-	-100	nA	$V_{CB} = -30\text{V}$
Emitter cutoff current	$I_{EBO}$	-	-	-100	nA	$V_{EB} = -6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-200	-370	mV	$I_C = -1\text{A}, I_B = -50\text{mA}$
DC current gain	$h_{FE}$	270	-	680	-	$V_{CE} = -2\text{V}, I_C = -100\text{mA}^*$
Transition frequency	$f_T$	-	280	-	MHz	$V_{CE} = -2\text{V}, I_E = 100\text{mA}, f = 100\text{MHz}^*$
Collector output capacitance	$C_{ob}$	-	13	-	pF	$V_{CB} = -10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$

\* Pulsed

Transistors

●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
QST7		○

●Electrical characteristic curves

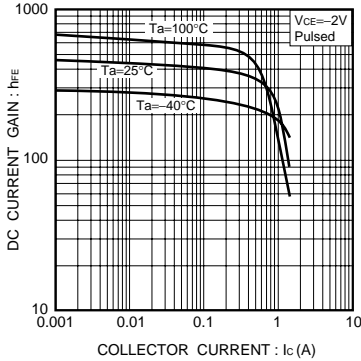


Fig.1 DC current gain vs. collector current

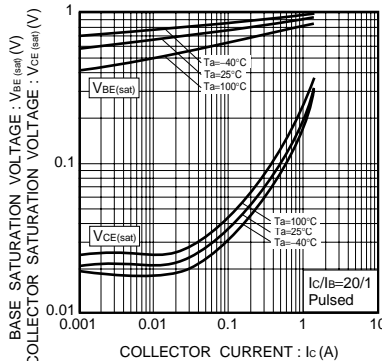


Fig.2 Collector-emitter saturation voltage base-emitter saturation voltage vs. collector current

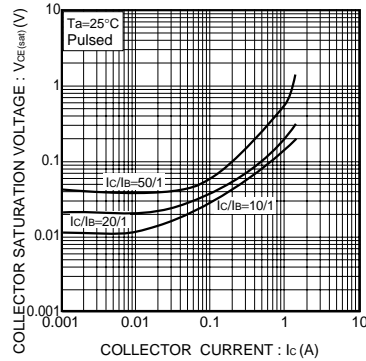


Fig.3 Collector-emitter saturation voltage vs. collector current

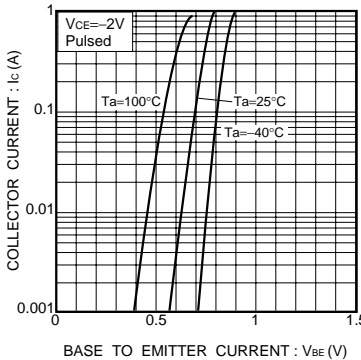


Fig.4 Grounded emitter propagation characteristics

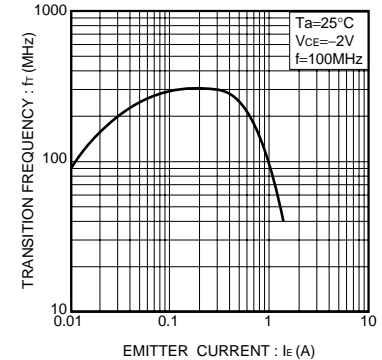


Fig.5 Gain bandwidth product vs. emitter current

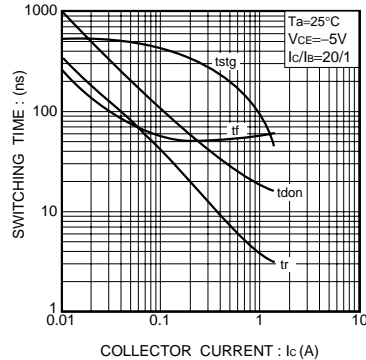


Fig.6 Switching time

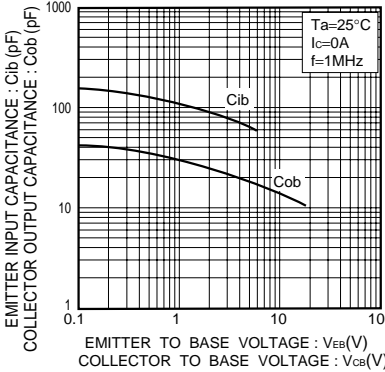


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

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